An all-electrical scheme for valley polarization in graphene

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We propose an all-electrical setup for achieving valley polarization in graphene. The setup consists of a finite graphene sheet connected to normal metal electrodes on both sides, with the junctions aligned along the zigzag edges while the armchair edges remain free. Each normal metal has two terminals, and when a bias is applied at one terminal while keeping the other three grounded, valley polarization arises due to transverse momentum matching between graphene and the normal metal. The valley polarization is maximized when the Fermi wave vector of the normal metal is approximately half the separation between the K and K' valleys in graphene. We analyze the dependence of conductance and valley polarization on system parameters such as the width and length of the graphene sheet, as well as the chemical potentials of graphene and the normal metal. The conductance through graphene increases with its width, while an increase in length initially reduces the conductance before leading to oscillatory behavior due to Fabry-Pérot interference. The valley polarization efficiency decreases with increasing graphene length due to inter-valley mixing from back-and-forth reflections within the graphene region. Furthermore, we investigate the impact of disorder in graphene and find that while conductance near the Dirac point increases with disorder strength due to enhanced density of states, valley polarization efficiency decreases due to intervalley scattering. Our results provide insights into controlling valley polarization in graphene-based devices for valleytronic applications.

I. INTRODUCTION

Over the past two decades, study of graphene [1] has emerged as a prominent area in condensed matter physics due to its remarkable properties. This two-dimensional material consists of carbon atoms arranged in a honeycomb lattice, with two atoms per unit cell. Its electronic structure features valence and conduction bands that meet at zero energy, forming Dirac points and exhibiting a linear dispersion relation. This unique band structure leads to intriguing quantum phenomena, such as Klein tunneling, making graphene a widely studied system. The zero-energy points in graphene's band structure, where the conduction and valence bands touch, are known as valleys. Each valley possesses distinct physical characteristics and responds differently to external influences such as polarized light. This property forms the foundation of valley tronics—an emerging field where the valley degree of freedom is exploited as an information carrier.

Graphene's band structure contains two inequivalent valleys, labeled K and K', which represent different points in momentum space. These valleys play a crucial role in the material's electronic properties and serve as fundamental elements in valleytronics. The ability to manipulate charge carriers within these valleys opens new avenues for electronic and quantum applications. An imbalance in the occupation of states in the two valleys is termed valley polarization. Such selective occupation can be induced by external factors like circularly polarized light, magnetic fields, or mechanical strain, which direct charge carriers into specific valleys. Valley polarization is central to valley tronics, adding a third dimension to conventional electronics (based on charge transport) and spintronics (which utilizes electron spin). This additional control over electronic states enables advancements in electronics, quantum computing [2], optoelectronics [3], and energy-efficient devices.

Various methods have been proposed to achieve valley polarization in graphene. Strain and symmetry-breaking potentials have been shown to induce valley polarization in graphene quantum dots [4]. A valley-polarized current has been proposed using gate voltage in a graphene np-n transistor [5]. Superconductors have been explored for detecting valley polarization [6]. In biased bilayer graphene, a band gap is introduced, and circularly polarized light of the right frequency can generate valley polarization [7]. Additionally, terahertz electromagnetic radiation has been demonstrated to filter electrons based on their valley index, leading to valley polarization [8, 9].

In junctions between two-dimensional materials, electron transmission from one side of the junction to the other occurs when momentum along the junction direction matches on both sides [10–12]. Building on this principle, we propose a setup to achieve valley polarization in graphene. The system consists of a graphene lattice placed between two normal metal sheets, as shown in Fig. 1. The normal metal is modelled by a square lattice. The graphene lattice is positioned such that its zigzag edges form junctions with the normal metals, while its armchair edges remain free. A bias is applied from terminal-1, while terminals 2, 3, and 4 are grounded. On the left normal metal, a net current flows along the y-direction, leading to an asymmetric occupation of k_y states, where positive values of k_u are favored over negative values. If the band structures of graphene and the normal metal are arranged such that the separation between the K and K' points in graphene is approximately

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equal to $2k_{y,F}$, where $k_{y,F}$ is the Fermi wave number in the y-direction for the normal metal, valley polarization can be achieved. Although the system lacks full translational invariance in any direction, we expect the physics of transverse momentum matching to hold as the width of the graphene region increases.



FIG. 1. Schematic of the normal metal/graphene/normal metal junction

II. THE SYSTEM AND THE CENTRAL IDEA

A graphene lattice of length L_{gx} and width L_{gy} is connected to normal metal square lattices on both sides, as illustrated in Fig. 1. The normal metal extends infinitely along the *y*-direction and has a finite width L_{nx} along the *x*-direction. The hopping strength within graphene is denoted by γ , considering only nearest-neighbor hopping. In the square lattice representing the normal metal, the hopping strength is *t*. The system is characterized by chemical potentials μ_n and μ_g for the normal metal and graphene, respectively, where the chemical potential in graphene can be tuned via an external gate voltage.

To analyze transport properties, we compute the differential conductance $G_j = dI_j/dV_1$, where I_j is the current in terminal j in response to an applied voltage V_1 at terminal 1, while terminals 2, 3, and 4 are kept grounded. The conductance contribution from the current flowing through the graphene region is given by $G_g = G_1 - G_2$. We employ the Landauer-Büttiker scattering theory to calculate these conductances.

Furthermore, we decompose the conductance contribution from graphene into components associated with the K and K' valleys, denoted as $G_{g,K}$ and $G_{g,K'}$, respectively. The valley polarization efficiency η is then defined as

$$\eta = \frac{2(G_{g,K} - G_{g,K'})}{G_{g,K} + G_{g,K'}}$$

This quantity serves as a measure of the extent to which valley polarization is achieved in the proposed setup.



FIG. 2. Dispersion of graphene and normal metal fixing $k_x = 0$.

The key mechanism for achieving valley polarization in this setup is the matching of transverse momenta between graphene and the normal metal. This is illustrated in Fig. 2, where the energy E is plotted as a function of k_y for $k_x = 0$ in both graphene and the normal metal. Within the bias window, the values of k_y in graphene and the normal metal are nearly identical, facilitating valley polarization.

III. RESULTS

Varying the chemical potential of the normal metal, μ_n , alters the size of its Fermi surface. Figure 3(a) shows the conductance through graphene, G_g , and the valley polarization efficiency, η , as functions of μ_n , while keeping other parameters fixed. In Fig. 3, the Fermi surfaces of the normal metal and graphene are depicted for (b) $\mu = -1.4$ eV and (c) $\mu = -4$ eV. In case (b), the Fermi surfaces of graphene and the normal metal share a larger range of k_y , leading to high conductance through graphene, as seen in Fig. 3(a). In contrast, for case (c), the mismatch in k_y values results in lower conductance through graphene.

Despite the lower conductance in case (c), the valley polarization efficiency remains high because states in the K valley are closer to the positive k_y states of the normal metal compared to those in the K' valley. Near the crossover region, as μ increases, the occupied states in the K valley of graphene have higher magnitude of velocity in the y-direction compared to that in x-direction, leading to back-and-forth reflections within graphene along ydirection, in addition to transmission along x-direction. These reflections cause mixing between the K and K' valley states, reducing the valley polarization efficiency. Consequently, around $\mu = -1.5$ eV in Fig. 3(a), η drops.

Another way to understand this drop is by considering the conductance through graphene, $G_g \approx G_{g,K} + G_{g,K'}$,



FIG. 3. (a) Conductance through graphene (right axis) and valley polarization efficiency (left axis) versus μ_n at zeros bias. Parameters: $t = 1.2eV, L_{nx} = 20, L_{gy} = 24, L_{gx} = 24, \mu_g = 0.5eV, \gamma = 2.7eV$. The Fermi surfaces of normal metal (dashed line) and graphene (solid line) for (b) $\mu = -1.4eV$ (c) $\mu = -4eV$.

which is very small for lower μ . Since this term appears in the denominator of the expression for η , the valley polarization efficiency is initially high. As μ increases near the crossover, G_g increases, but the difference $G_{g,K} - G_{g,K'}$ does not significantly grow due to back-and-forth scattering in the y-direction within graphene, leading to the observed drop in η . Beyond the crossover, further increases in μ enhance both the conductance through graphene and the valley polarization efficiency, as transverse momentum matching improves over a wider range of k_y .

The hypothesis that back-and-forth reflections within graphene along the y-direction lead to mixing between the two valleys can be tested by analyzing the dependence of conductance and valley polarization efficiency on L_{gx} and L_{gy} . As L_{gy} increases while keeping L_{gx} fixed, both the conductance through graphene and the valley polarization efficiency increase overall, as shown in Fig. 4(a,b). In contrast, as L_{gx} increases (for a fixed L_{gy}), the conductance through graphene initially decreases and then oscillates around a certain value, while the valley polarization efficiency, η , decreases overall.

Among the many conduction channels in graphene, some have energies outside the bias window. In these channels, conduction occurs via evanescent modes, leading to a decrease in conductance with increasing L_{gx} . However, in other channels where conduction occurs through plane-wave modes, the conductance exhibits os-



FIG. 4. (a) Conductance through graphene G_g versus L_{gy} , (b) Valley polarization effeciency η versus L_{gy} , (c) G_g versus L_{gx} , (d) η versus L_{gx} . Parameters: (a,b) $L_{gx} = 24$, (c,d) $L_{gy} = 24$. $t = 1.2 \ eV$, $\mu = -1.4 \ eV$, $\mu_g = 0.5 \ eV$.



FIG. 5. Conductance G_g and valley polarization efficiency η versus the chemical potential of graphene μ_g . Parameters: $\mu = -1.4 \ eV$, $L_{gx} = L_{gy} = 24$, $L_{nx} = 20$.

cillations as a function of L_{gx} . As a result, the overall conductance initially decreases with L_{gx} and then oscillates. Meanwhile, the valley polarization efficiency decreases due to the increasing number of back-and-forth reflections along the *y*-direction, which become more prominent as L_{qx} grows.

Next, we examine the dependence of conductance through graphene and valley polarization efficiency on the chemical potential of graphene, μ_g , as shown in Fig. 5. The conductance, G_g , decreases and tends to zero as μ_g approaches the Dirac point ($\mu_g = 0$), exhibiting oscillations in the process. In sufficiently large samples, zero conductance at $\mu_g = 0$ is expected due to the vanishing density of states at the Dirac point. As μ_g moves



FIG. 6. (a,c) Conductance through graphene versus disorder strength. (b,d) Valley polarization efficiency versus disorder strength. Both physical quantities are averaged over 100 disorder configurations and the error-bar shows the standard deviation about the mean. Parameters: $L_{gx} = 24$, $L_{gy} = 24$ $t = 1.2 \ eV$, $\mu = -1.4 \ eV$. For (a,b), $\mu_g = 0.5 eV$, for (c,d) $\mu_g = 0.2 eV$.

away from the Dirac point, the density of states increases, leading to a corresponding increase in conductance. This rise in conductance away from the Dirac point is accompanied by oscillations, which can be attributed to Fabry-Pérot interference of plane-wave modes within graphene [10, 11, 13]. The valley polarization efficiency shoots up to large values near $\mu_g = 0$, but at these values, the conductance through graphene is very small making valley polarization not of much importance.

Next, we introduce on-site disorder in the graphene region, where the disorder potential is randomly distributed within the range [-w/2, w/2]. The resulting conductance and valley polarization efficiency are plotted in Fig. 6. We observe that the conductance increases with disorder strength for $\mu_g = 0.2$ eV and $\mu_g = 0.5$ eV [see Fig. 6(a,c)]. This behavior can be attributed to the low density of states near the charge neutrality point in graphene–introducing disorder enhances the density of states, thereby increasing conductance. However, valley polarization is suppressed by disorder [see Fig. 6(b,d)], as impurity scattering leads to mixing between states from

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the two valleys, reducing the extent of valley polarization.

IV. SUMMARY

We propose an all-electrical setup to achieve valley polarization in graphene. In this configuration, a graphene sheet is connected to normal metals on either side, with each normal metal having two terminals. A bias applied at one terminal while keeping the other three grounded leads to valley polarization when the Fermi wave vector in the normal metal is approximately half the separation between the K and K' valleys in graphene.

We analyze the dependence of valley polarization on the geometric parameters of the system. Our results show that both the conductance through graphene and the valley polarization increase with the width of the graphene sheet. In contrast, as the length of the graphene sheet increases, the conductance initially decreases and then oscillates around a steady value, while the valley polarization efficiency decreases.

Additionally, we investigate the effect of disorder on valley polarization by introducing on-site disorder in the graphene region. We find that while increasing disorder strength leads to enhanced conductance near the Dirac point—due to an increase in the density of states—it simultaneously reduces valley polarization. This suppression occurs because disorder-induced scattering mixes states from the two valleys, diminishing the polarization efficiency.

Our findings demonstrate a viable approach to achieving and controlling valley polarization in graphene using an all-electrical setup, with potential implications for valleytronic applications.

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Appendix A: Details of calculation

Figure 1 illustrates the schematic of the model, where a finite graphene sheet is connected to two normal metals (NMs). These normal metals, modeled as square lattices, have a finite number of sites (L_{nx}) along the x-direction, while they extend infinitely along the y-direction. As shown in the figure, the system consists of four terminals. When a bias is applied to terminal 1 while the other three terminals are grounded, a potential difference develops between terminal 1 and the other terminals. This potential difference drives a current from terminal 1 toward terminal 2, while also inducing currents in graphene toward terminals 3 and 4.

The Hamiltonian for the setup is given by:

$$H = H_L + H_{LG} + H_G + H_{GR} + H_R, \text{ where}$$
$$H_{LG} = -t' \sum_{n_y=1}^{L_{gy}} [(c_{L_{nx},n_y}^{\dagger} d_{1,n_y} + \text{h.c.}),$$
$$H_{GR} = -t' \sum_{i=1}^{L_{gy}} [d_{L_{ax},n_y}^{\dagger} c_{L_{nx}+1,n_y} + \text{h.c.}]$$

 $n_y = 1$

$$H_{L} = -t \sum_{n_{y}=-\infty}^{\infty} \left[\sum_{n_{x}=1}^{L_{nx}-1} \left[(c_{n_{x}+1,n_{y}}^{\dagger} c_{n_{x},n_{y}} + \text{h.c.}) \right] \right] \\ + \sum_{n_{x}=1}^{L_{nx}} \left[(c_{n_{x},n_{y}-1}^{\dagger} c_{n_{x},n_{y}} + \text{h.c.}) \right] \right] \\ -\mu_{n} \sum_{n_{x}=1}^{L_{nx}} \sum_{n_{y}=-\infty}^{\infty} c_{n_{x},n_{y}}^{\dagger} c_{n_{x},n_{y}} \\ H_{R} = -t \sum_{n_{y}=-\infty}^{\infty} \left[\sum_{n_{x}=L_{nx}+1}^{2L_{nx}-1} \left[(c_{n_{x}+1,n_{y}}^{\dagger} c_{n_{x},n_{y}} + \text{h.c.}) \right] \right] \\ + \sum_{n_{x}=L_{nx}+1}^{2L_{nx}} \left[(c_{n_{x},n_{y}-1}^{\dagger} c_{n_{x},n_{y}} + \text{h.c.}) \right] \right] \\ -\mu_{n} \sum_{n_{x}=L_{nx}+1}^{2L_{nx}} \sum_{n_{y}=-\infty}^{\infty} c_{n_{x},n_{y}}^{\dagger} c_{n_{x},n_{y}} \\ H_{G} = -\gamma \sum_{n_{x}=1}^{L_{gx}-1} \sum_{n_{y}=1}^{L_{gy}} \left[d_{n_{x}+1,n_{y}}^{\dagger} d_{n_{x},n_{y}} + \text{h.c.} \right] \\ -\gamma \sum_{n_{x}=1}^{\prime} \sum_{n_{y}=-1}^{L_{gy}-1} \left[d_{n_{x}+1,n_{y}}^{\dagger} d_{n_{x},n_{y}} + \text{h.c.} \right]$$

where c_{n_x,n_y} annihilates an electron at site (n_x, n_y) in normal metal, d_{n_x,n_y} annihilates an electron on site (n_x, n_y) in graphene, t is the hopping strength in the normal metal, t' is the hopping strength at the junction of the normal metal and graphene, and μ_n is the chemical potential in the normal metal, γ is the hopping strength in graphene, μ_g is the chemical potential in graphene, $\sum_{n_x=4n+m}'$ means the summation is over all integers between 1 to L_{gx} having the form (4n + m), where n is a nonnegative integer and m = 2,3. We take graphene to be composed of spinless electrons. We set t' = t in numerical calculations. The labelling of sites on the graphene lattice follows the scheme shown in Fig. 7 for lattice of size $(L_{gx}, L_{gy}) = (16, 3)$.

In each of the four terminals of the normal metal, the modes are described by the wavenumber k_m in the *y*-direction, which satisfies the dispersion relation

$$E = -2t\cos\left(k_mb\right) + \epsilon_m - \mu_n,\tag{A2}$$

for $m = 1, 2, ..., L_{nx}$, where b is the lattice constant in the normal metal. Here, ϵ_m are the eigenenergies of a one-dimensional Hamiltonian along the x-direction with



FIG. 7. Scheme for labelling the lattice sites in graphene.

open boundary conditions, having L_{nx} sites and a hopping strength of t. As a result, each of the four terminals supports L_{nx} transport channels.

The column vector v_m , of size $L_{nx} \times 1$, represents the eigenstate of the one-dimensional Hamiltonian corresponding to the eigenenergy ϵ_m . At a given energy E, the wavenumber k_m may be real or complex. An electron can be incident from channel m_0 of terminal 1 only if k_{m_0} is real.

The scattering eigenfunction corresponding to an electron with energy E incident on the system is expressed as

$$|\psi\rangle = \sum_{n_x, n_y} \psi_{n_x, n_y, n} |n_x, n_y, n\rangle + \sum_{n_x, n_y} \psi_{n_x, n_y, g} |n_x, n_y, g\rangle.$$
(A3)

Here, $\psi_{n_x,n_y,n}$ can be grouped into column vectors ψ_{n_y,n_t} with L_{nx} entries, where the n_x -th entry is equal to $\psi_{n_x,n_y,n}$ in terminals $n_t = 1, 2$, and the n_x -th entry is equal to $\psi_{L_{nx}+n_x,n_y,n}$ in terminals $n_t = 3, 4$. The wave function ψ_{n_y,n_t} takes the form:

$$\psi_{n_y,1} = v_{m_0} e^{ik_{m_0}n_y b} + \sum_{m=1}^{L_{nx}} r_{m,m_0} v_m e^{-ik_m n_y b},$$

for $n_y \le 0,$
$$\psi_{n_y,2} = \sum_{m=1}^{L_{nx}} t_{m,m_0,2} v_m e^{ik_m n_y b}, \text{ for } n_y > L_{gy},$$

$$\psi_{n_y,3} = \sum_{m=1}^{L_{nx}} t_{m,m_0,3} v_m e^{ik_m n_y b}, \text{ for } n_y > L_{gy},$$

$$\psi_{n_y,4} = \sum_{m=1}^{L_{nx}} t_{m,m_0,4} v_m e^{-ik_m n_y b}, \text{ for } n_y \le 0.$$

(A4)

The scattering coefficients r_{m,m_0} , $t_{m,m_0,j}$ (for j = 2, 3, 4) and the wavefunctions $\psi_{n_x,n_y,g}$ can be determined using the Schrödinger wave equation $H|\psi\rangle = E|\psi\rangle$.

The differential conductivity $G_j = dI_j/dV$, the differential ratio of the current in terminal j to the voltage bias V applied in terminal-1 is given by:

$$G_{j} = \frac{e^{2}}{h} \sum_{m_{0}}^{\prime} \frac{1}{\sin k_{m_{0}} a} \sum_{m}^{\prime} |t_{m,m_{0}}^{j}|^{2} \sin k_{m} a, \quad (A5)$$

$$(\text{for } j = 2, 3, 4),$$

$$G_{1} = \frac{e^{2}}{h} \sum_{m_{0}}^{\prime} \left[1 - \sum_{m}^{\prime} \frac{|r_{m,m_{0}}|^{2} \sin k_{m} a}{\sin k_{m_{0}} a} \right],$$

$$(A6)$$

where the primed summation over m means that the summation is done over all the values of m for which k_m is real. The conductances obey the conservation condition $G_1 = G_2 + G_3 - G_4$. The conductance through graphene is given by $G_g = G_1 - G_2 = G_3 - G_4$.

To characterize the valley polarization, we consider the momentum eigenstates of the graphene lattice, denoted as $\phi_{\vec{k}}$, which have the same dimensions as the graphene region in the setup and satisfy periodic boundary conditions within the first Brillouin zone. The states near the K-point are classified as belonging to the K valley, while those near the K'-point are assigned to the K' valley.

Let $\psi(m_0, E)$ represent a current-carrying eigenstate of the scattering problem corresponding to an electron incident in the m_0 -th transport channel at energy E. The graphene component of this scattering eigenfunction, normalized over the graphene region, is denoted as $\psi^g(m_0, E)$. If $G_g(m_0, E)$ is the contribution of the m_0 th channel to the total conductance through graphene, then the contribution of a particular momentum state \vec{k} in graphene to this conductance is given by

$$G_g(m_0, E) |\phi_{\vec{k}}^{g\dagger} \cdot \psi^g(m_0, E)|^2.$$

The valley polarised conductance which is defined as the difference between conductance contributions from states belonging to K and K' valleys is then given by

$$G^{g,V} = \sum_{m_0}' G_g(m_0, E) \cdot \left[\sum_{\vec{k} \in K} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2 - \sum_{\vec{k} \in K'} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2\right]$$
(A7)

The valley polarization efficiency η defined as the ratio of difference between the contributions of K and K' valleys to conductance through graphene to the sum of the contributions of K and K' valleys to conductance through graphene is given by

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$$\eta = \frac{\sum_{m_0}' G_g(m_0, E) \cdot \left[\sum_{\vec{k} \in K} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2 - \sum_{\vec{k} \in K'} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2\right]}{\sum_{m_0}' G_g(m_0, E) \cdot \left[\sum_{\vec{k} \in K} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2 + \sum_{\vec{k} \in K'} |\phi_{\vec{k}}^{\dagger} \cdot \psi^g(m_0, E)|^2\right]}$$
(A8)